



PRODUCT NAME : MCR100 0.8A 600V SCR

PRICE : Rs 35.00

SKU : RM1951



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DESCRIPTION

Features

- Gate Turn-On Voltage (Vgt): 0.8V
- Peak Off-State Voltage(Vdrm): 600V
- On-State Current (It): 0.8A
- Gate Current (Igt): 200μA

MOTOROLA
SEMICONDUCTOR TECHNICAL DATA

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 by MCR100/D

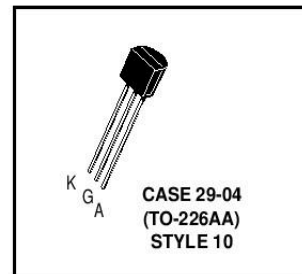
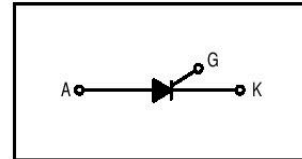
Silicon Controlled Rectifiers
Reverse Blocking Triode Thyristors

PNPN devices designed for high volume, line-powered consumer applications such as relay and lamp drivers, small motor controls, gate drivers for larger thyristors, and sensing and detection circuits. Supplied in an inexpensive plastic TO-226AA package which is readily adaptable for use in automatic insertion equipment.

- Sensitive Gate Trigger Current — 200 μ A Maximum
- Low Reverse and Forward Blocking Current — 100 μ A Maximum, $T_C = 125^\circ\text{C}$
- Low Holding Current — 5 mA Maximum
- Glass-Passivated Surface for Reliability and Uniformity

MCR100
Series*
 *Motorola preferred devices

SCRs
0.8 AMPERE RMS
100 thru 600 VOLTS



MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted.)

Rating	Symbol	Value	Unit
Peak Repetitive Forward and Reverse Blocking Voltage ⁽¹⁾ ($T_J = 25$ to 125°C , $R_{GK} = 1 \text{ k}\Omega$) MCR100-3 MCR100-4 MCR100-6 MCR100-8	V_{DRM} and V_{RRM}	100 200 400 600	Volts
Forward Current RMS (See Figures 1 & 2) (All Conduction Angles)	$I_T(\text{RMS})$	0.8	Amps
Peak Forward Surge Current, $T_A = 25^\circ\text{C}$ (1/2 Cycle, Sine Wave, 60 Hz)	I_{TSM}	10	Amps
Circuit Fusing Considerations ($t = 8.3 \text{ ms}$)	I^2t	0.415	A^2s
Peak Gate Power — Forward, $T_A = 25^\circ\text{C}$	P_{GM}	0.1	Watts
Average Gate Power — Forward, $T_A = 25^\circ\text{C}$	$P_{GF(AV)}$	0.01	Watt
Peak Gate Current — Forward, $T_A = 25^\circ\text{C}$ (300 μs , 120 PPS)	I_{GFM}	1	Amp
Peak Gate Voltage — Reverse	V_{GRM}	5	Volts
Operating Junction Temperature Range @ Rated V_{RRM} and V_{DRM}	T_J	-40 to +125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to +150	$^\circ\text{C}$
Lead Solder Temperature ($< 1/16"$ from case, 10 s max)	—	+230	$^\circ\text{C}$

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Preferred devices are Motorola recommended choices for future use and best overall value.



MCR100 Series

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	75	$^{\circ}C/W$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$, $R_{GK} = 1\text{ k}\Omega$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
Peak Forward or Reverse Blocking Current ($V_{AK} = \text{Rated } V_{DRM} \text{ or } V_{RRM}$)	I_{DRM}, I_{RRM}	—	10 100	μA μA
Forward "On" Voltage ⁽¹⁾ ($I_{TM} = 1\text{ A Peak @ } T_A = 25^{\circ}C$)	V_{TM}	—	1.7	Volts
Gate Trigger Current (Continuous dc) ⁽²⁾ (Anode Voltage = 7 Vdc, $R_L = 100\text{ Ohms}$)	I_{GT}	—	200	μA
Gate Trigger Voltage (Continuous dc) (Anode Voltage = 7 Vdc, $R_L = 100\text{ Ohms}$) (Anode Voltage = Rated V_{DRM} , $R_L = 100\text{ Ohms}$)	V_{GT}	— — 0.1	0.8 1.2 —	Volts
Holding Current (Anode Voltage = 7 Vdc, initiating current = 20 mA)	I_H	— —	5 10	mA

1. Forward current applied for 1 ms maximum duration, duty cycle $\leq 1\%$.
2. R_{GK} current is not included in measurement.

FIGURE 1 – MCR100-7, MCR100-8 CURRENT DERATING (REFERENCE: CASE TEMPERATURE)

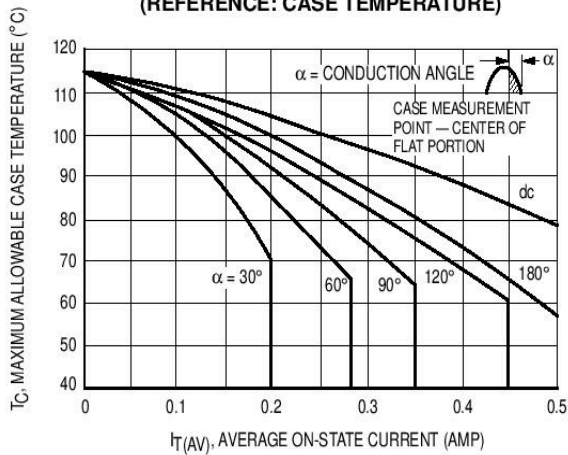


FIGURE 2 – MCR100-7, MCR100-8 CURRENT DERATING (REFERENCE: AMBIENT TEMPERATURE)

